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Semiconductor devices –

Part 16-1: Microwave integrated circuits – Amplifiers

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SEMICONDUCTOR DEVICES –

Part 16-1: Microwave integrated circuits – Amplifiers

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The technical content is therefore identical to the base edition and its amendment and has been prepared for user convenience.

It bears the edition number 1.1.

A vertical line in the margin shows where the base publication has been modified by amendment 1.

The committee has decided that the contents of the base publication and its amendments will remain unchanged until the maintenance result date indicated on the IEC web site under "<http://webstore.iec.ch>" in the data related to the specific publication. At this date, the publication will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

A bilingual version of this standard may be issued at a later date.

SEMICONDUCTOR DEVICES –

Part 16-1: Microwave integrated circuits – Amplifiers

1 Scope

This part of IEC 60747 provides the terminology, the essential ratings and characteristics, as well as the measuring methods for integrated circuit microwave power amplifiers.

2 Normative references

The following referenced documents are indispensable for the application of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60617:2001, *Graphical symbols for diagrams*

IEC 60747-1:2006, *Semiconductor devices – Part 1: General*

IEC 60747-4:-, *Semiconductor devices – Discrete devices – Part 4: Microwave diodes and transistors*¹

IEC 60747-7:2000, *Semiconductor devices – Part 7: Bipolar transistors*

IEC 60747-16-2:2001, *Semiconductor devices – Part 16-2: Microwave integrated circuits – Frequency prescalers*

IEC 60747-16-4:2004, *Semiconductor devices – Part 16-4: Microwave integrated circuits – Switches*

IEC 60748-2:1997, *Semiconductor devices – Integrated circuits – Part 2: Digital integrated circuits*

IEC 60748-3:1986, *Semiconductor devices – Integrated circuits – Part 3: Analogue integrated circuits*

IEC 60748-4:1997, *Semiconductor devices – Integrated circuits – Part 4: Interface integrated circuits*

IEC/TS 61340-5-1:1998, *Electrostatics - Part 5-1: Protection of electronic devices from electrostatic phenomena - General requirements*

IEC/TS 61340-5-2:1999, *Electrostatics - Part 5-2: Protection of electronic devices from electrostatic phenomena - User guide*

¹ The second edition of IEC 60747-4, which is cited in this standard, and to which terms introduced in this amendment refer, is currently in preparation (ADIS).